

**OSG55R380FF\_Datasheet**

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

## Applications

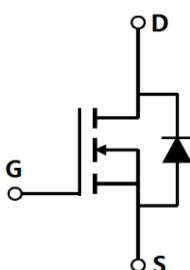
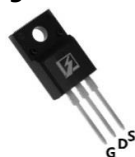
- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

## ■ General Description

OSG55R380FF uses advanced GreenMOSTM technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@Tjmax}$	600 V
◆ $I_{D, pulse}$	33 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	380 mΩ
◆ $Q_g$	12.5 nC

## ■ Schematic and Package Information

<b>Schematic Diagram</b> 	<b>Pin Assignment Top View</b>  <b>TO220F</b> <b>OSG55R380FF</b>
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## ■ Absolute Maximum Ratings at $T_j=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	550	V
Gate source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup>	$I_D$	11	A
Continuous drain current <sup>1)</sup> $T_j=100^{\circ}C$		7	
Pulsed drain current <sup>2)</sup>	$I_{D, pulse}$	33	A
Power dissipation <sup>3)</sup>	$P_D$	28	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	200	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0...440 V$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0...440 V, I_{SD} \leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^{\circ}C$

## ■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	4.5	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$

## ■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	550			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
		600				$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$ $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.30	0.38	$\Omega$	$V_{GS}=10\text{ V}, I_D=5.5\text{ A}$
			0.79			$V_{GS}=10\text{ V}, I_D=5.5\text{ A},$ $T_j=150^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=550\text{ V}, V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		549.3		pF	$V_{GS}=0\text{ V},$ $V_{DS}=50\text{ V},$ $f=1\text{ MHz}$
Output capacitance	$C_{oss}$		63.1		pF	
Reverse transfer capacitance	$C_{rss}$		2.1		pF	
Turn-on delay time	$t_{d(on)}$		28.0		ns	$V_{GS}=10\text{ V},$ $V_{DS}=400\text{ V},$ $R_G=2\ \Omega,$ $I_D=6\text{ A}$
Rise time	$t_r$		22.8		ns	
Turn-off delay time	$t_{d(off)}$		60.3		ns	
Fall time	$t_f$		18.0		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		12.5		nC	$I_D=6\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		2.6		nC	
Gate-drain charge	$Q_{gd}$		5.7		nC	
Gate plateau voltage	$V_{\text{plateau}}$		5.8		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	$I_S$			11	A	$V_{GS} < V_{th}$
Pulsed source current	$I_{SP}$			33		
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=11\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		199.0		ns	$V_R=400\text{ V}$ , $I_S=6\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		1.7		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		17.4		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $R_G=25\text{ }\Omega$ ,  $L=10\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

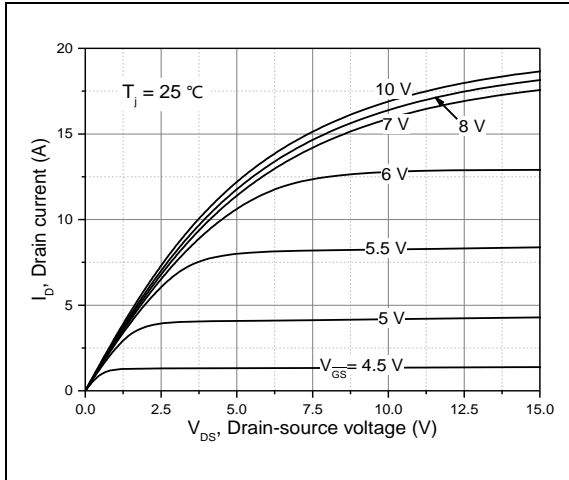


Figure 1, Typ. output characteristics

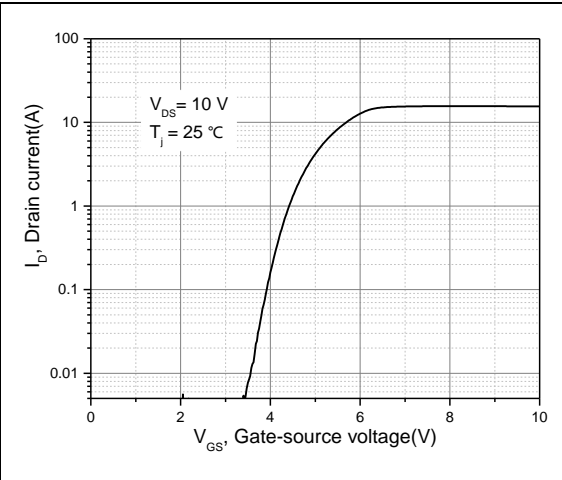


Figure 2, Typ. transfer characteristics

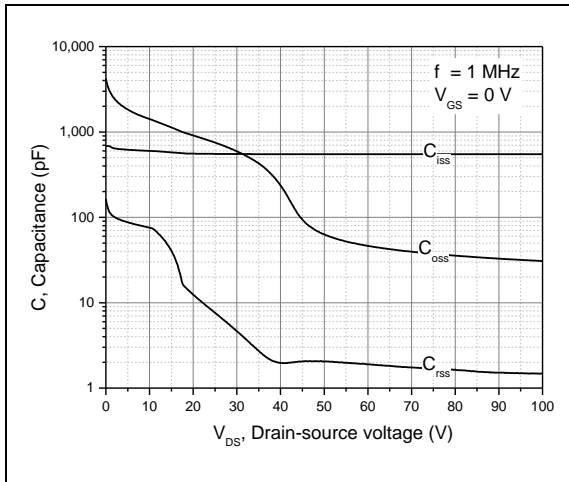


Figure 3, Typ. capacitances

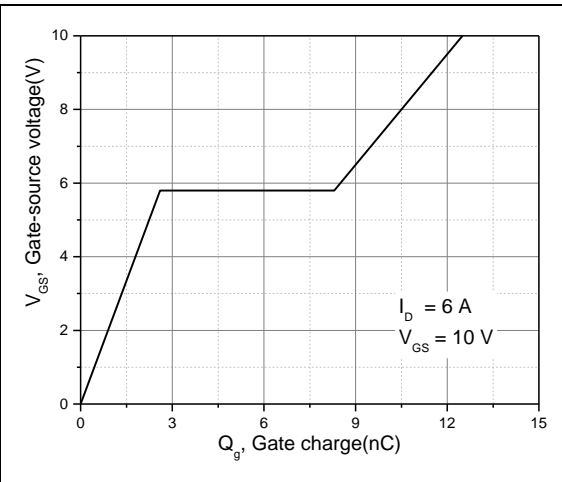


Figure 4, Typ. gate charge

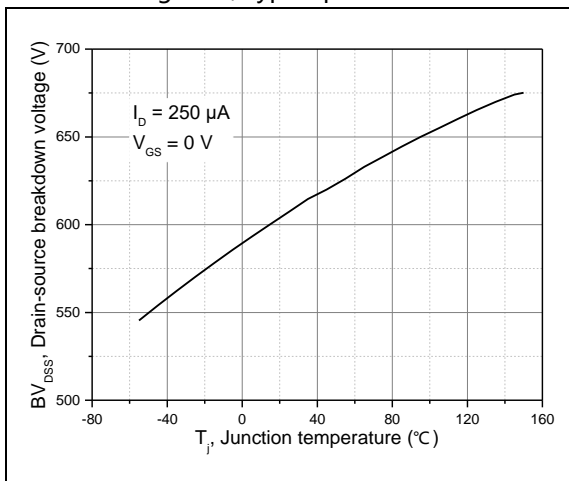


Figure 5, Drain-source breakdown voltage

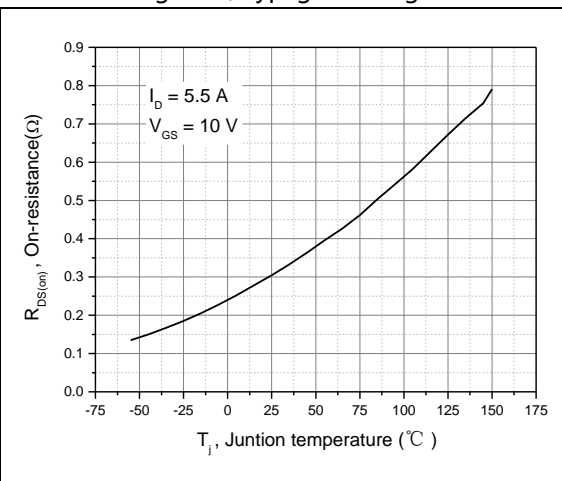


Figure 6, Drain-source on-state resistance

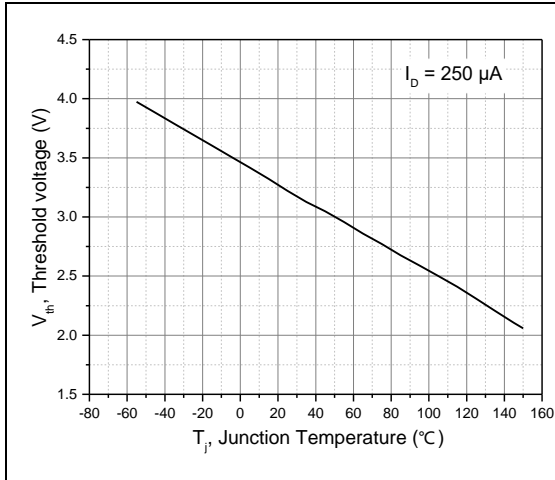


Figure 7, Threshold voltage

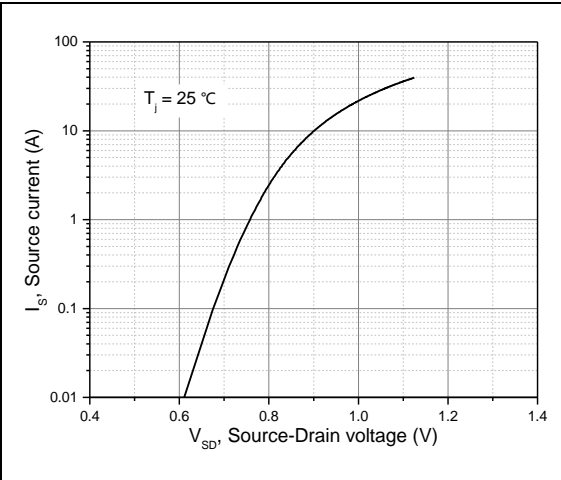


Figure 8, Forward characteristic of body diode

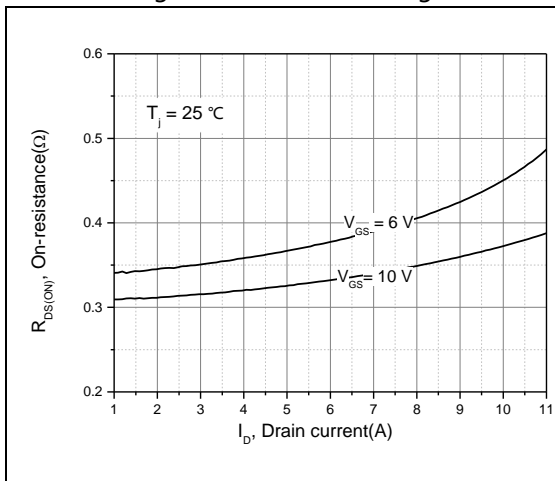


Figure 9, Drain-source on-state resistance

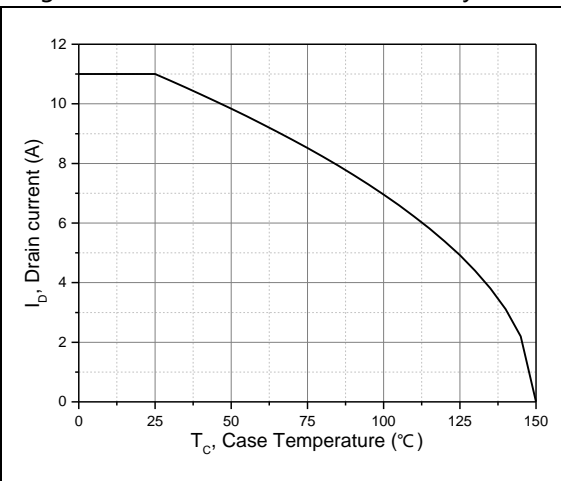


Figure 10, Drain current

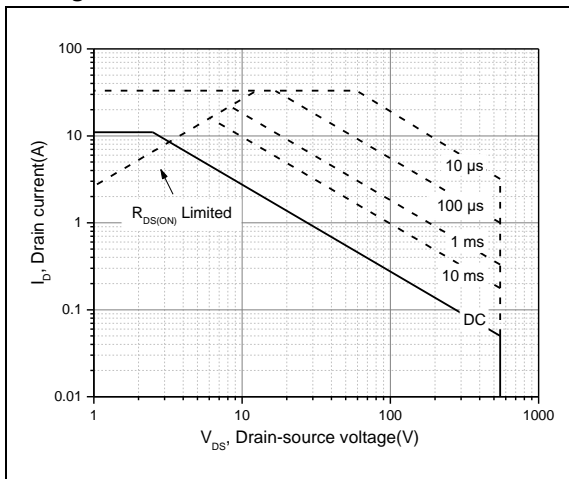


Figure 11, Safe operation area for TO220F  
TC=25 °C

■ Test circuits and waveforms

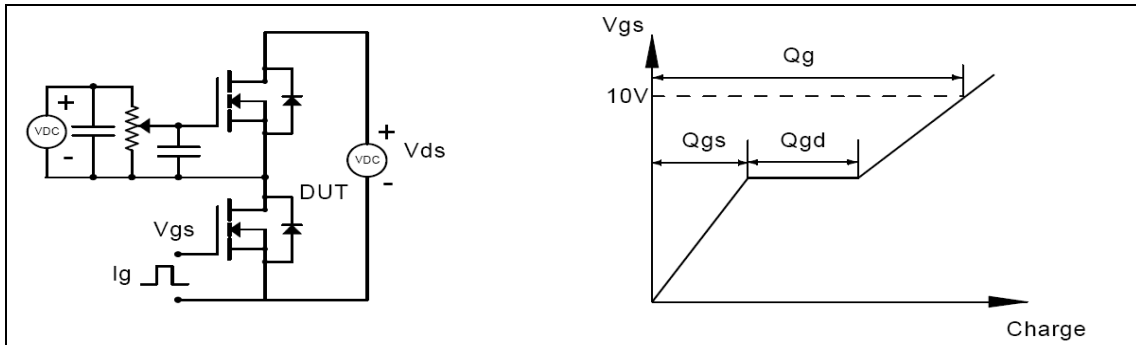


Figure 1, Gate charge test circuit & waveform

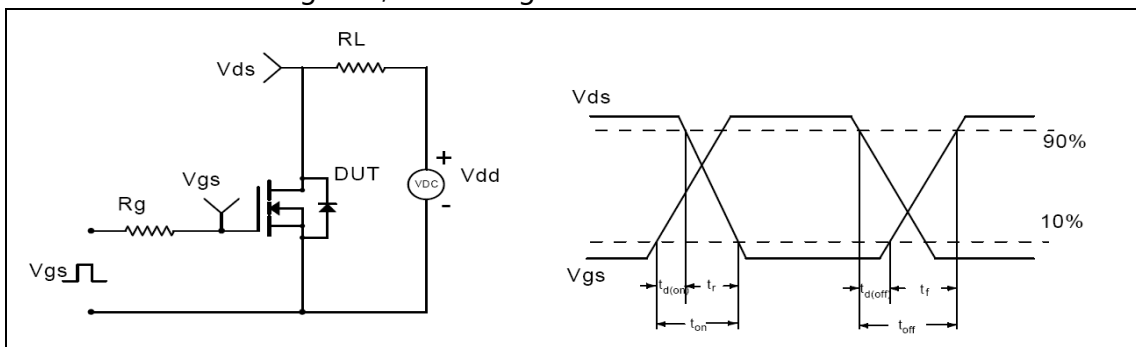


Figure 2, Switching time test circuit & waveforms

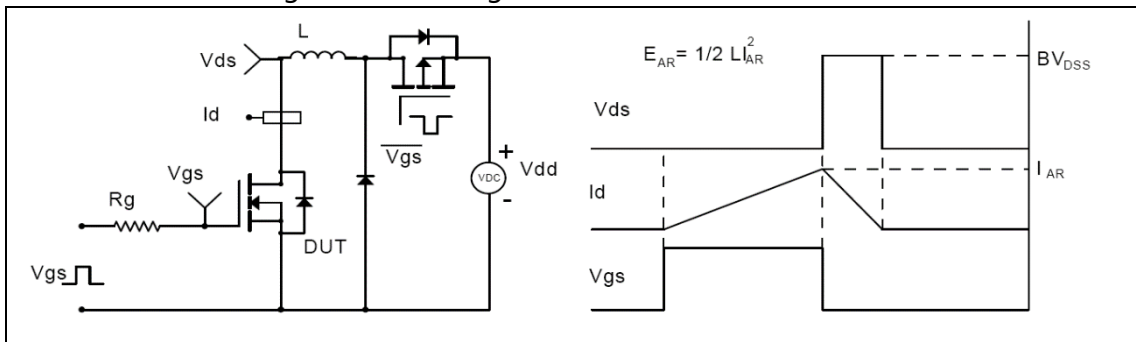


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

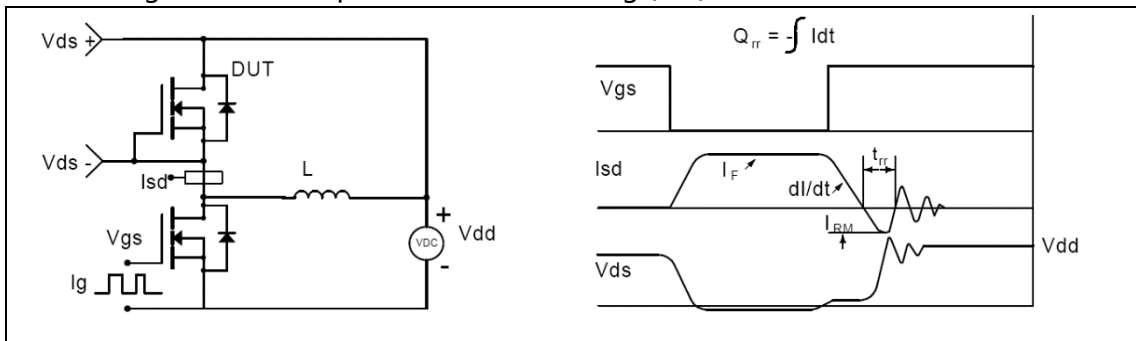
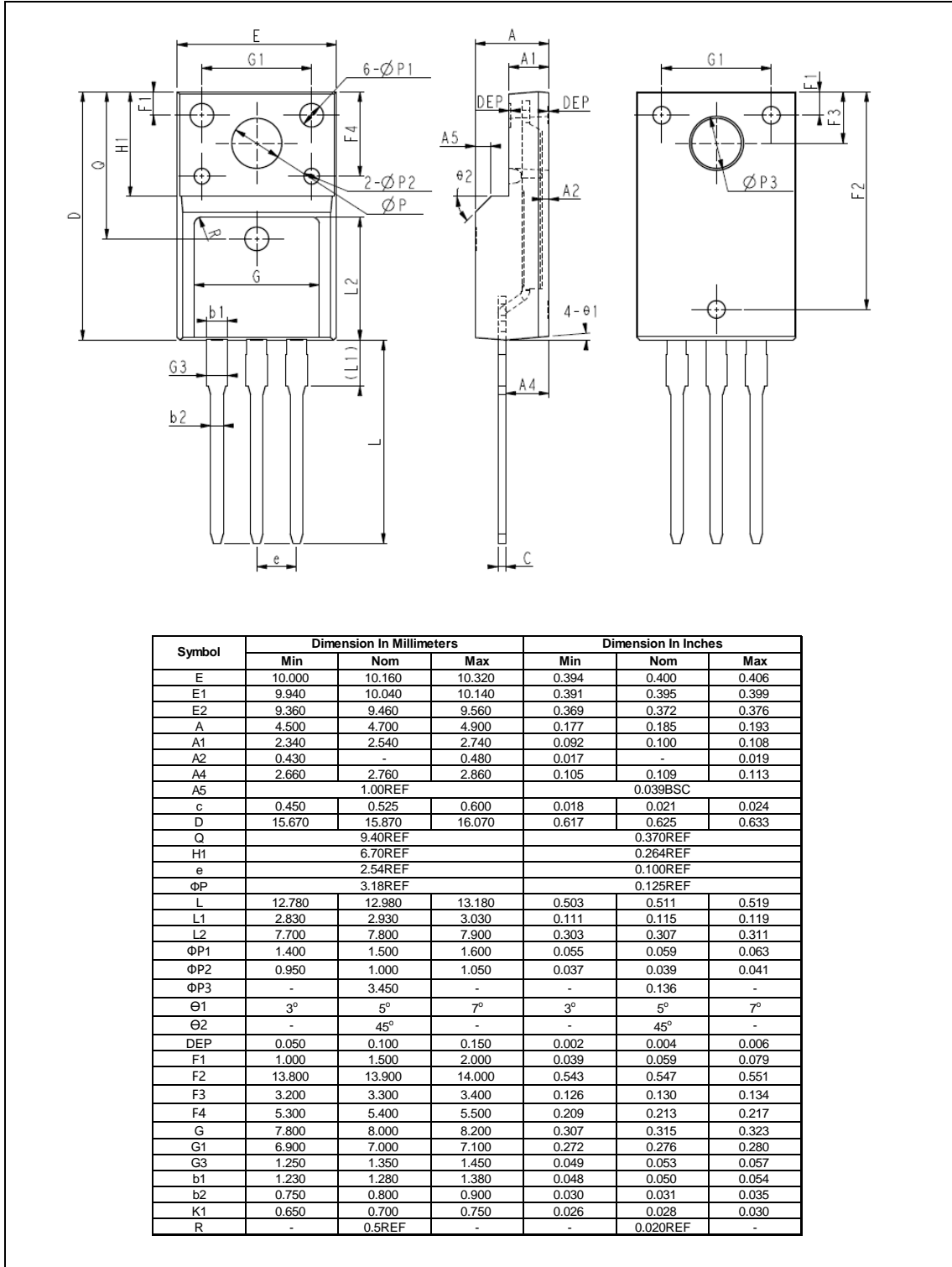


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

Figure1, TO220F package outline dimension





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**■ Ordering Information**

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Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO220F	50	20	1000	6	6000

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**■ Product Information**

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Product	Package	Pb Free	RoHS	Halogen Free
OSG55R380FF	TO220F	yes	yes	yes